ROHM

4.5V to 28V Input, 8.0A Integrated MOSFET Single Synchronous Buck DC/DC Converter

BD9F800MUX-Z

General Description

BD9F800MUX-Z is a synchronous buck DC/DC converter with built-in low on-resistance power MOSFETs. It is capable of providing current of up to 8 A. External phase compensation circuit is not necessary for it is a constant on-time control DC/DC converter with high speed response.

Features

- Synchronous Single DC/DC Converter
- **Constant On-time Control**
- **Over Current Protection**
- Short Circuit Protection
- **Thermal Shutdown Protection**
- Under Voltage Lockout Protection
- Power Good Output
- VQFN11X3535A Package

Applications

- Step-down Power Supply for DSPs,
- Microprocessors, etc.
- Set-top Box
- LCD TVs
- DVD / Blu-ray Player / Recorder
- **Entertainment Devices**

Key Specifications

- Input Voltage Range:
- 4.5V to 28 V Output Voltage Setting Range: 0.765V to 13.5V
- Output Current: 8 A (Max)
- Switching Frequency: 300kHz or 600kHz (Typ)
- High Side MOSFET On-Resistance: 23 m Ω (Typ)
- Low Side MOSFET On-Resistance: $11 \text{ m } \Omega$ (Typ)
- Shutdown Current: 2 µA (Typ)

Package W (Typ) \times D (Typ) \times H (Max) VQFN11X3535A 3.50mm × 3.50mm × 0.60mm



Typical Application Circuit

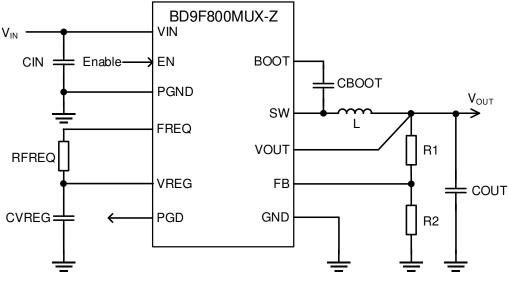
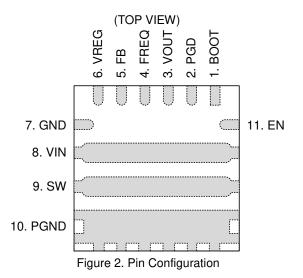


Figure 1. Typical Application Circuit

OProduct structure: Silicon monolithic integrated circuit OThis product has no designed protection against radioactive rays.

Pin Configuration



Pin Descriptions

Terminal No.	Symbol	Function
1	BOOT	Bootstrap terminal. Connect a ceramic capacitor of 0.1μ F between BOOT and SW terminal. The voltage of this capacitor is the gate drive voltage of the High-Side MOSFET.
2	PGD	Power Good terminal. It is necessary to connect a pull-up resistor due to an open drain output. See page 19 for how to specify the resistance. When the FB terminal voltage is within $\pm 7\%$ of 0.765V (Typ), the internal Nch MOSFET turns off and the output turns High.
3	VOUT	Output voltage sense terminal. Connect a 10Ω resistor in series when output voltage setting is more than 3.3V.
4	FREQ	Switching frequency setting terminal. Switching frequency is set to 300kHz when this terminal is set to Low (0.8V or lower). Setting this terminal to High (2.2V or higher) will make switching frequency set to 600kHz. This terminal needs to be pulled down to ground or pulled up to VREG by $10k\Omega$.
5	FB	An inverting input node for the error amplifier and main comparator. To calculate for the resistance value of the output voltage setting, refer to page 39.
6	VREG	Internal power supply voltage terminal. A voltage of 5.25V (Typ) is outputted if there is more than 2.3V for EN terminal. Connect a ceramic capacitor of 2.2 μ F to ground.
7	GND	Ground terminal for the control circuit.
8	VIN	Power supply terminal for the switching regulator. Connecting $20\mu F(10\mu F \times 2)$ and $0.1\mu F$ ceramic capacitor to ground is recommended.
9	sw	Switch terminal. The SW terminal is connected to the source of the High-Side MOSFET and drain of the Low-Side MOSFET. Connect a bootstrap capacitor of 0.1μ F between BOOT and SW terminal. Also, connect an inductor considering the direct current superimposition characteristic.
10	PGND	Ground terminal for the output stage of the switching regulator.
11	EN	Enable terminal. Turning this terminal signal Low (0.7V or lower) forces the device to enter in shutdown mode. Turning this terminal signal High (2.3V or higher) enables the device. This terminal must be properly terminated.

Block Diagram

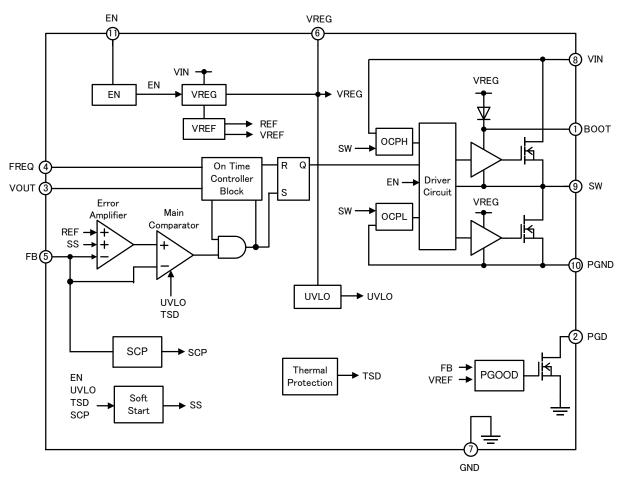


Figure 3. Block Diagram

Description of Blocks

• EN

The device will shut down when EN falls to 0.7V (Max) or lower. When EN reaches 2.3V (Min), the internal circuit is activated and the device starts up.

• VREG

The VREG block generates the internal power supply.

- VREF The VREF block generates the internal reference voltage.
- Error Amplifier Error Amplifier adjusts Main Comparator input to make internal reference voltage equal to FB terminal voltage.
- Main Comparator
 Main comparator

Main comparator compares Error Amplifier output and FB terminal voltage. When FB terminal voltage becomes low, it outputs High and reports to the On Time block that the output voltage has dropped below control voltage.

- ON Time Controller Block This block generates ON Time. The desired ON Time is generated when Main Comparator output becomes High. ON Time is adjusted to restrict frequency change even with Input / Output voltage change.
- Soft Start

The Soft Start circuit slows down the rise of output voltage during start-up and controls the current, which allows the prevention of output voltage overshoot and inrush current. The internal soft start time is set to 1ms typically.

PGOOD

When the FB terminal voltage reaches within \pm 7% of 0.765V(Typ), the built-in open drain output Nch MOSFET turns off and the output goes high.

Driver Circuit

This block is a DC/DC driver. A signal from ON Time Controller Block is applied to drive the MOSFETs.

• UVLO

UVLO is a protection circuit that prevents low voltage malfunction. It prevents malfunction of the internal circuit from sudden rise and fall of power supply voltage. When VIN voltage is higher than 4.2V (Typ), UVLO is released and the soft-start circuit will be started. This threshold voltage has a hysteresis of 400mV (Typ). When VIN voltage is less than 3.8V (Typ), the device will shut down.

TSD

The TSD block is for thermal protection. The thermal protection circuit shuts down the device when the internal temperature of device rises to 175°C (Typ) or higher. Thermal protection circuit resets when the temperature falls. The circuit has a hysteresis of 25°C (Typ).

SCP

After the soft start is completed and when the FB terminal voltage has fallen below 0.38V (Typ) for 250µs (Typ), the SCP stops the operation for 8ms (Typ) and subsequently initiates restart.

OCPH

When inductor current exceeds the current limit threshold value while High-Side MOSFET is ON, the High-Side MOSFET will turn OFF.

OCPL

The OCP function limits the current flowing through the Low-Side MOSFET for every switching period. If the inductor current exceeds the source current limit threshold value I_{OCP} while Low-Side MOSFET is ON, the Low-Side MOSFET remains ON even with FB voltage is lower than the REF voltage. The Low-Side MOSFET keeps ON until inductor current becomes lower than I_{OCP} and High-Side MOSFET will turn ON. The Low-Side MOSFET will turn OFF when inductor current exceeds the sink current limit threshold value while Low-Side MOSFET is ON.

Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rating	Unit
Input Voltage	VIN	-0.3 to +30	V
Voltage from GND to BOOT	VBOOT	-0.3 to +35	V
Voltage from SW to BOOT	VBOOT - VSW	-0.3 to +7	V
SW Terminal Voltage	Vsw	-0.3 to V _{IN} + 0.3	V
FB Terminal Voltage	V _{FB}	-0.3 to V _{VREG}	V
VREG Terminal Voltage	V _{VREG}	-0.3 to +6	V
FREQ Terminal Voltage	VFREQ	-0.3 to +7	V
VOUT Terminal Voltage	Vvout	-0.3 to +20	V
PGD Terminal Voltage	VPGD	-0.3 to +35	V
EN Terminal Voltage	V _{EN}	-0.3 to +30	V
Maximum Junction Temperature	Tjmax	150	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Caution 1: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

Caution 2: Should by any chance the maximum junction temperature rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. In case of exceeding this absolute maximum rating, increase the board size and copper area to prevent exceeding the maximum junction temperature rating.

Thermal Resistance^(Note 1)

Devemeter	Symbol	Thermal Res	Linit		
Parameter	Symbol	1s ^(Note 3)	2s2p ^(Note 4)	Unit	
VQFN11X3535A					
Junction to Ambient	θја	232.1	48.0	°C/W	
Junction to Top Characterization Parameter ^(Note 2)	Ψ_{JT}	44.2	8.2	°C/W	

(Note 1) Based on JESD51-2A(Still-Air).

(Note 2) The thermal characterization parameter to report the difference between junction temperature and the temperature at the top center of the outside surface of the component package.

(Note 3) Using a PCB board based of	n JESD51-3.	
Layer Number of Measurement Board	Material	Board Size
Single	FR-4	114.3mm x 76.2mm x 1.57mmt
Тор		
Copper Pattern	Thickness	
Footprints and Traces	70µm	

(Note 4) Using a PCB board based on JESD51-7.

Layer Number of	Material	Board Size		Thermal Via ^(Note 5)		
Measurement Board	Material	Duaru Size		Pitch	Diameter	
4 Layers	FR-4	114.3mm x 76.2mm x 1.6mmt		1.20mm Ф0.30mm		
Тор		2 Internal Layers		Bottom		
Copper Pattern Thickness		Copper Pattern	Thickness	Copper Pattern	n Thickness	
Footprints and Traces	70µm	74.2mm x 74.2mm	35µm	74.2mm x 74.2m	im 70µm	

(Note 5) This thermal via connects with the copper pattern of all layers.

Recommended Operating Conditions

Parameter	Symbol	Min	Тур	Max	Unit
Input Voltage	VIN	4.5	12	28	V
Operating Temperature Range	Topr	-40	-	+85 (Note 1)	°C
Output Current	Іоит	0	-	8	А
Output Voltage Range	VRANGE	0.765 (Note 2)	-	13.5 (Note 3)	V

(Note 1) Tj must be lower than 150°C under actual operating environment. Life time is derated at junction temperature greater than 125°C.

(Note 2) Please use under the condition of $V_{OUT} \ge V_{IN} \times 0.033$ [V] (300kHz), $V_{OUT} \ge V_{IN} \times 0.067$ [V] (600kHz). (Note 3) Please use under the condition of $V_{OUT} \le V_{IN} \times 0.87$ -0.12×I_{OUT} [V](300kHz), $V_{OUT} \le V_{IN} \times 0.77$ -0.13×I_{OUT} [V](600kHz).

(Refer to the page 39 for how to calculate the output voltage setting.)

Electrical Characteristics (Ta = 25°C, VIN = 12V, VEN = 3V, FREQ=L unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Shutdown Current	Isd	-	2	15	μA	V _{EN} =GND
Operating Circuit Current	I _{VIN}	-	0.85	1.6	mA	Iout=0mA when no switching
EN Low Voltage	VENL	-	-	0.7	V	
EN High Voltage	VENH	2.3	-	VIN	V	
EN Input Current	I _{EN}	-	2.5	10	μA	V _{EN} =3V
FREQ Low Voltage	VFREQL	-	-	0.8	V	
FREQ High Voltage	VFREQH	2.2	-	VVREG	V	
FREQ Input Current	IFREQ	-	1.5	5	μA	V _{FREQ} =3V
VREG Shutdown Voltage	Vvreg_sd	-	-	0.1	V	V _{EN} =GND
VREG Output Voltage	VVREG	5	5.25	5.5	V	
VREG Output Current	I _{REG}	-	10	-	mA	
UVLO Threshold Voltage	V _{UVLO}	3.9	4.2	4.5	V	VIN:Sweep up
UVLO Hysteresis Voltage	VUVLO_HYS	200	400	600	mV	
FB Terminal Voltage	V _{FB}	0.757	0.765	0.773	V	V _{IN} =12V, V _{OUT} =1.0V
FB Input Bias Current	IFB	-	-	1	μA	
Soft Start Time	tss	0.5	1	2	ms	
On Time1	ton1	-	277	-	ns	V _{IN} =12V, V _{OUT} =1.0V, FREQ=L
On Time2	ton2	-	150	-	ns	V _{IN} =12V, V _{OUT} =1.0V, FREQ=H
Minimum Off Time	t MINOFF	-	250	-	ns	
High Side FET ON Resistance	Ronh	-	23	-	mΩ	
Low Side FET ON Resistance	Ronl	-	11	-	mΩ	
Current Limit Threshold	IOCP	-	11.5	-	А	(Note 4)
Power Good Falling (Fault) Voltage	VPGDFF	87	90	93	%	FB falling
Power Good Rising (Good) Voltage	Vpgdrg	90	93	96	%	FB rising
Power Good Rising (Fault) Voltage	Vpgdrf	107	110	113	%	FB rising
Power Good Falling (Good) Voltage	VPGDFG	104	107	110	%	FB falling
Power Good Output Leakage Current	ILKPGD	-	0	5	μA	PGD= 5V
Power Good ON Resistance	Rpgd	-	500	1000	Ω	
Hiccup Threshold Voltage	V _{HCP}	0.26	0.38	0.5	V	FB Terminal
Hiccup Delay Time	THCPDLY	-	250	-	μs	

(Note 4) No tested on outgoing inspection.

Typical Performance Curves

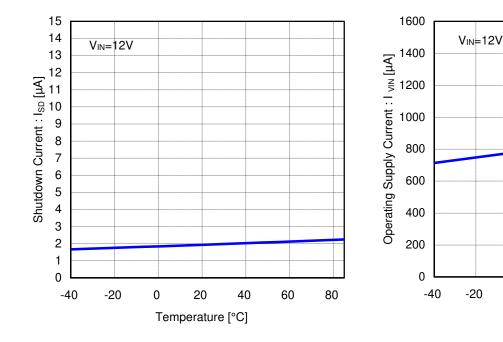


Figure 4. Shutdown Current vs Temperature

Figure 5. Operating Supply Current vs Temperature

20

Temperature [°C]

40

60

80

0

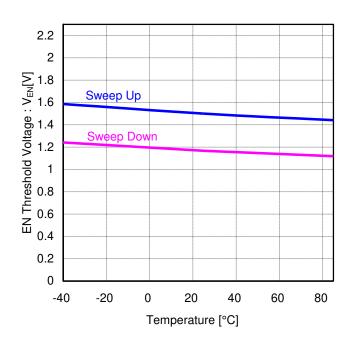


Figure 6. EN Threshold Voltage vs Temperature

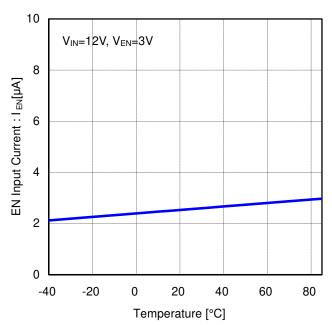


Figure 7. EN Input Current vs Temperature

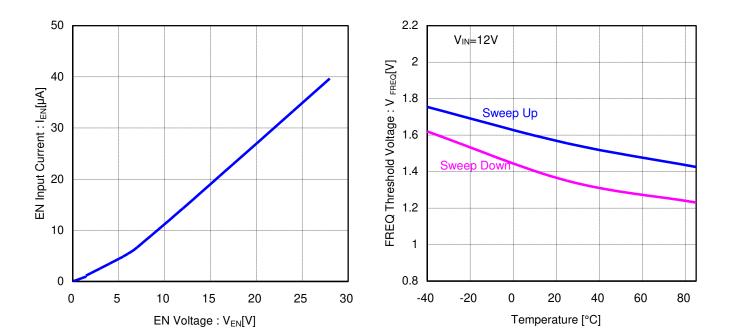


Figure 8. EN Input Current vs EN Voltage

Figure 9. FREQ Threshold Voltage vs Temperature

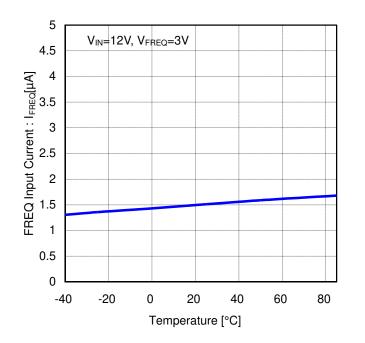


Figure 10. FREQ Input Current vs Temperature

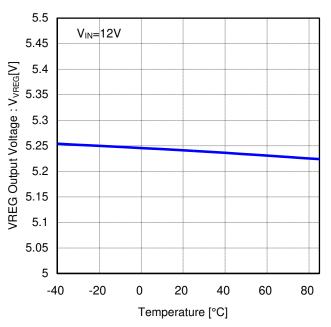


Figure 11. VREG Output Voltage vs Temperature

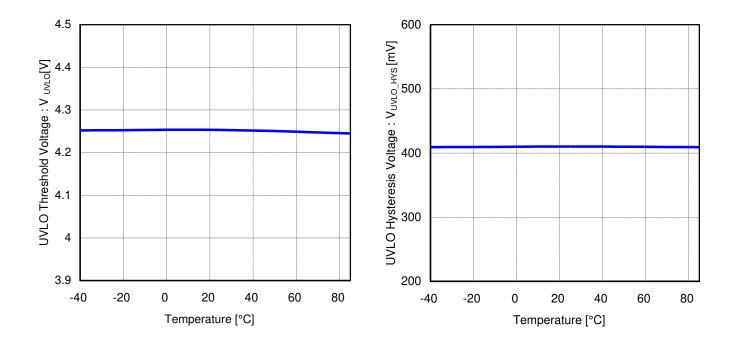


Figure 12. UVLO Threshold Voltage vs Temperature

Figure 13. UVLO Hysteresis Voltage vs Temperature

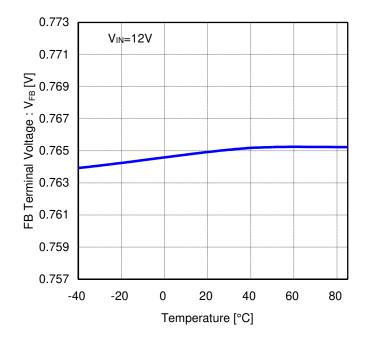


Figure 14. FB Terminal Voltage vs Temperature

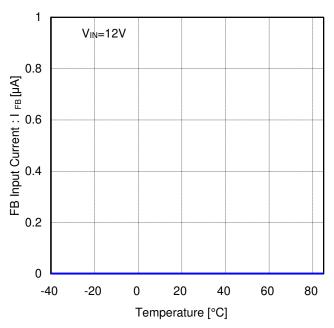


Figure 15. FB Input Current vs Temperature

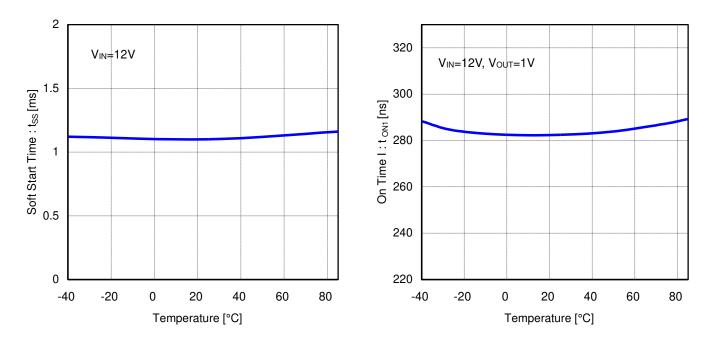


Figure 16. Soft Start Time vs Temperature

Figure 17. On Time 1 vs Temperature

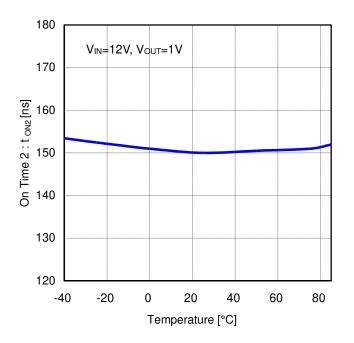


Figure 18. On Time 2 vs Temperature

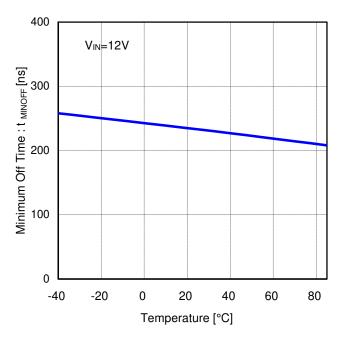


Figure 19. Minimum Off Time vs Temperature

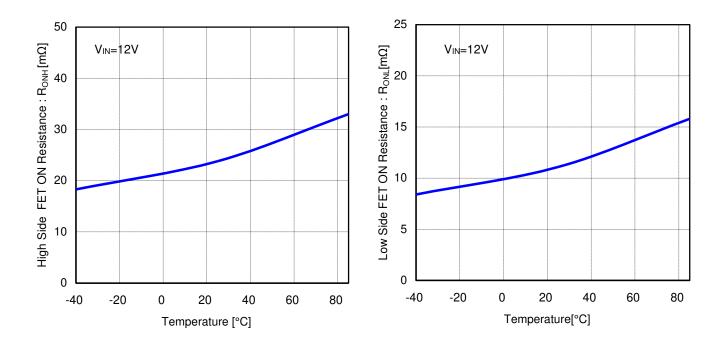


Figure 20. High Side FET ON Resistance vs Temperature

Figure 21. Low Side FET ON Resistance vs Temperature

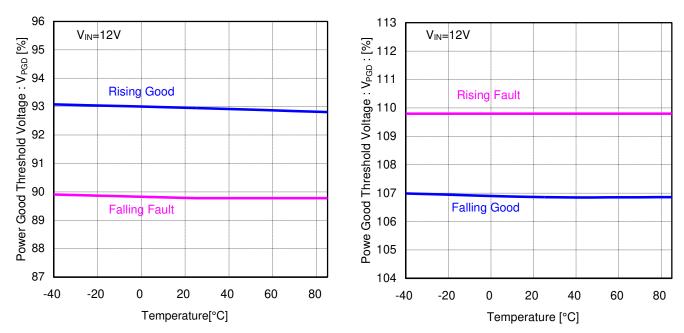


Figure 22. Power Good Threshold Voltage vs Temperature

Figure 23. Power Good Threshold Voltage vs Temperature

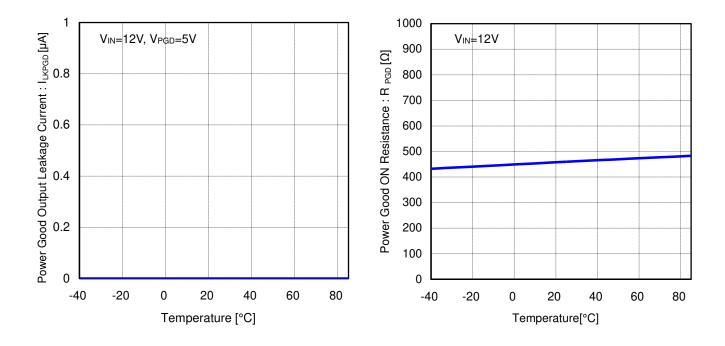


Figure 24. Power Good Output Leakage Current vs Temperature

Figure 25. Power Good ON Resistance vs Temperature

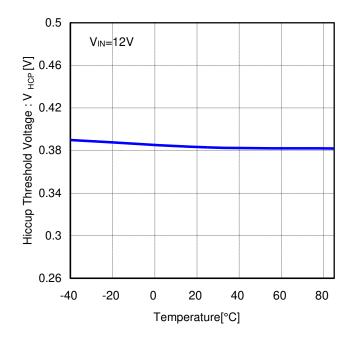


Figure 26. Hiccup Threshold Voltage vs Temperature

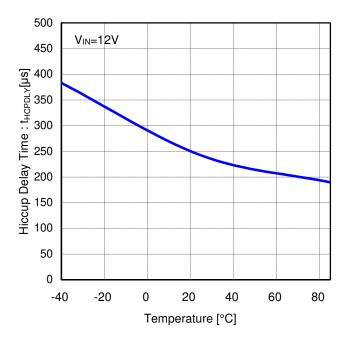


Figure 27. Hiccup Delay Time vs Temperature

10

9

8

7

6

5

4

3

2

1

0

-40

Output Current [A]

Typical Performance Curves - continued

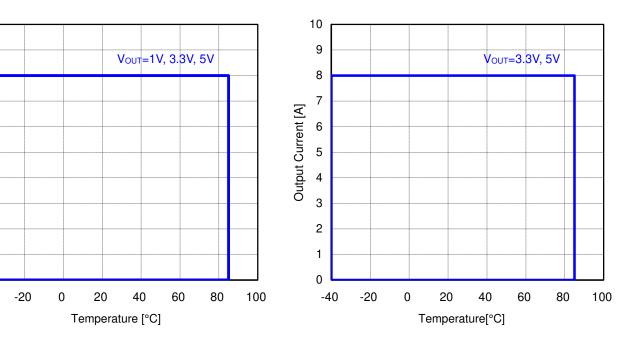
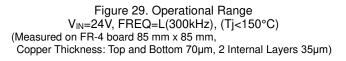
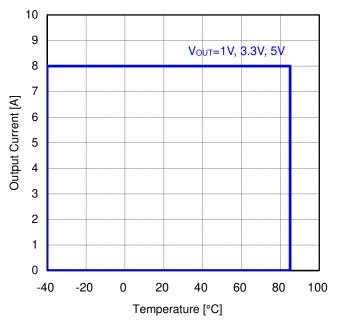
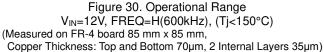


Figure 28. Operational Range V_{IN}=12V, FREQ=L(300kHz), (Tj<150°C) (Measured on FR-4 board 85 mm x 85 mm, Copper Thickness: Top and Bottom 70µm, 2 Internal Layers 35µm)







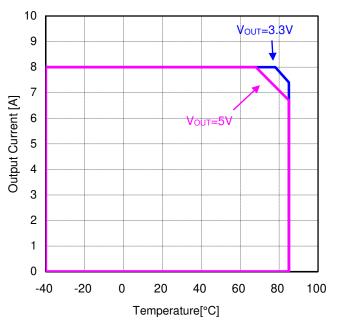


Figure 31. Operational Range V_{IN}=24V, FREQ=H(600kHz), (Tj<150°C) (Measured on FR-4 board 85 mm x 85 mm, Copper Thickness: Top and Bottom 70µm, 2 Internal Layers 35µm) BD9F800MUX-Z

Typical Performance Curves - continued

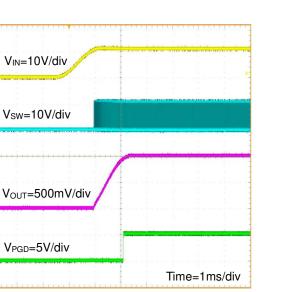


Figure 32. Start-up Waveform ($V_{IN}=V_{EN}$) ($V_{IN}=12V$, $V_{OUT}=1V$, FREQ=L(300kHz), RLOAD=0.125 Ω)

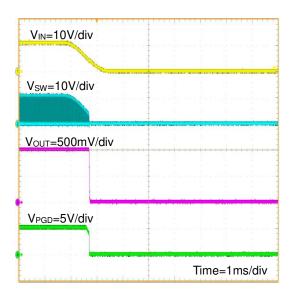


Figure 33. Shutdown Waveform (V_{IN}=V_{EN}) (V_{IN}=12V, V_{OUT}=1V, FREQ=L(300kHz), R_{LOAD}=0.125\Omega)

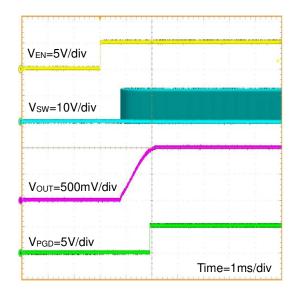


Figure 34. Start-up Waveform (V_{EN}=0V to 5V) (V_{IN}=12V, V_{OUT}=1V, FREQ=L(300kHz), R_{LOAD}=0.125 Ω)

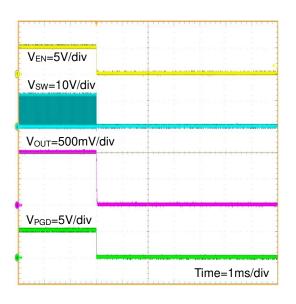
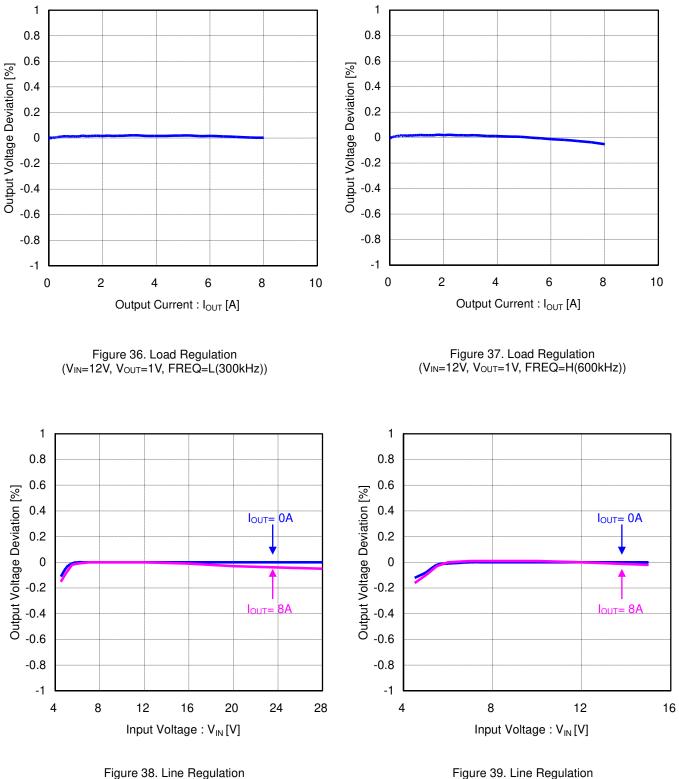
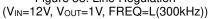
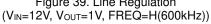


Figure 35. Shutdown Waveform (V_{EN}=5V to 0V) (V_{IN}=12V, V_{OUT}=1V, FREQ=L(300kHz), R_{LOAD}=0.125 Ω)







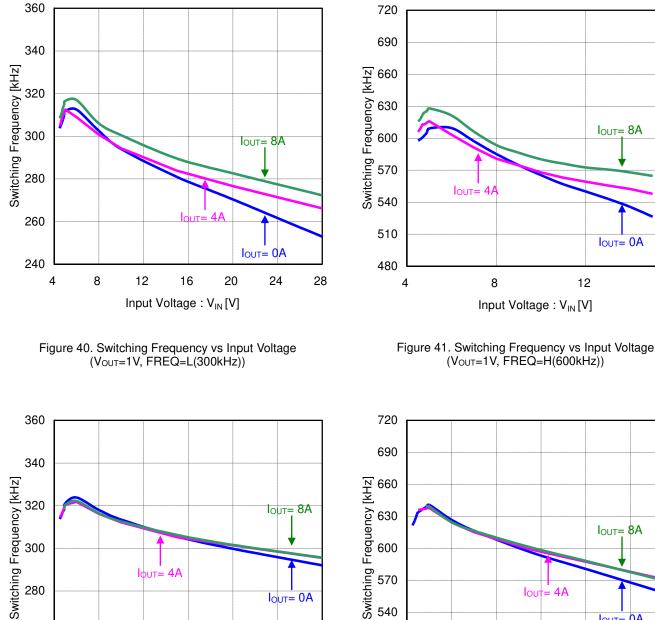
IOUT= 8A

IOUT= 0A

16

12

Typical Performance Curves - continued



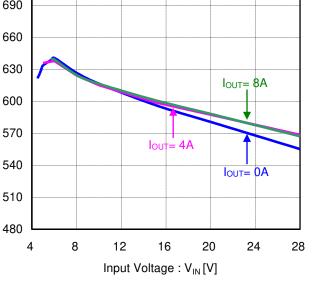


Figure 43. Switching Frequency vs Input Voltage (Vout=3.3V, FREQ=H(600kHz))

260

240

4

8

12

16

Input Voltage : VIN [V]

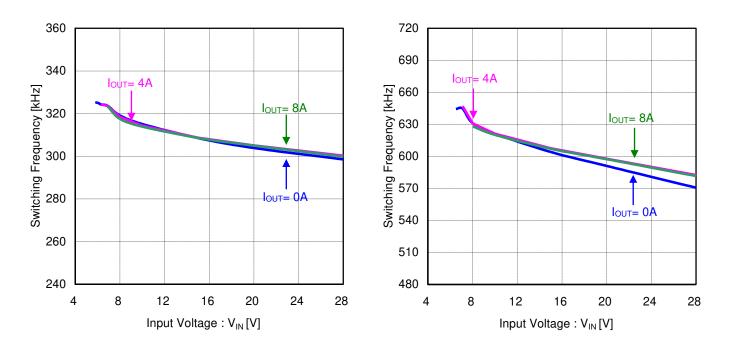
Figure 42. Switching Frequency vs Input Voltage

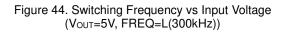
(Vout=3.3V, FREQ=L(300kHz))

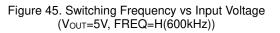
20

24

28







Function Explanations

1. Basic Operation

(1) Constant On Time Control

BD9F800MUX-Z is a single synchronous buck switching regulator employing a constant on-time control system. It controls the on-time by using the duty ratio of V_{OUT} / V_{IN} inside device so that a switching frequency becomes 300 kHz or 600 kHz. Therefore it runs with the frequency of 300 kHz or 600 kHz under the constant on-time decided with V_{OUT} / V_{IN} .

(2) Enable Control

The device shutdown can be controlled by the voltage applied to the EN terminal. When V_{EN} reaches 2.3 V(Min), the internal circuit is activated and the device starts up. To enable shutdown control with the EN terminal, the shutdown interval (Low level interval of EN) must be set to 100 μ s or longer. Startup by EN must be at the same time or after the input of power supply voltage.

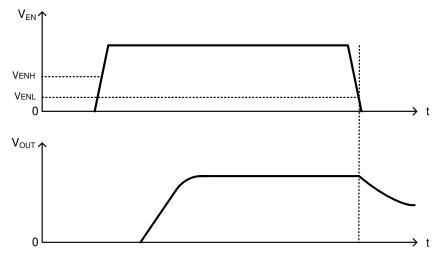


Figure 46. Start Up and Shut Down with Enable

(3) Soft Start

When EN terminal is turned High, Soft Start operates and output voltage gradually rises. With the Soft Start Function, over shoot of output voltage and rush current can be prevented. Rising time of output voltage is 1ms(Typ).

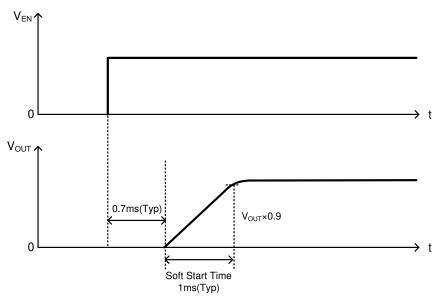


Figure 47. Soft Start Timing Chart

(4) Power Good Output

When the output voltage reaches within $\pm 7\%$ (Typ) of the set voltage, the open drain Nch MOSFET internally connected to the PGD terminal turns off and the PGD terminal goes into Hi-Z state. When the output voltage goes beyond $\pm 10\%$ (Typ) of the set voltage, the open drain Nch MOSFET turns on and PGD terminal turns Low by a 500 Ω (Typ) pull-down resistor. Connecting a pull up resistor of about $20k\Omega$ to $100k\Omega$ is recommended.

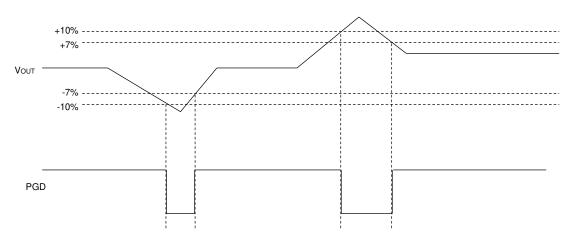


Figure 48. PGD Timing Chart

2. Protective Functions

The protective circuits are intended for prevention of damage caused by unexpected accidents. Do not use them for continuous protective operation.

(1) Over Current Protection, Short Circuit Protection (OCPL, SCP)

Over current protection function limits the current flowing through the Low-Side MOSFET for every switching period. If the inductor current exceeds the source current limit threshold value I_{OCP} 11.5A(Typ) while Low-Side MOSFET is ON, the Low-Side MOSFET remains ON even with FB voltage is lower than the REF voltage. The Low-Side MOSFET keeps ON until inductor current becomes lower than I_{OCP} and High-Side MOSFET will turn ON. As a result both frequency and duty fluctuates and output voltage may decrease.

In a case where output decreases because of OCP, output may rise after OCP is released due to the action at high speed load response.

When the FB voltage falls below 0.38V(Typ) and its state continues for 250µs(Typ), the operation stops and restart in hiccup mode after 8 ms(Typ).

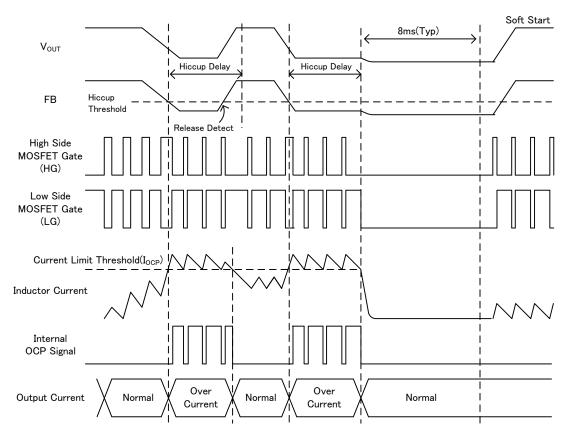


Figure 49. Over current protection timing chart

(2) Low Side Sink Over Current Protection (RCP)

When inductor current exceeds the sink current limit threshold value of 3.5A(Typ) while Low-Side MOSFET is ON, the Low-Side MOSFET will turn OFF.

(3) High Side Over Current Protection (OCPH)

When inductor current exceeds the current limit threshold value of 15.5A(Typ) while High-Side MOSFET is ON, the High-Side MOSFET will turn OFF.

(4) Under Voltage Lockout Protection (UVLO) The operation enters standby when the VIN terminal voltage is 3.8 V (Typ) or lower. The operation starts when the VIN terminal voltage is 4.2 V (Typ) or higher. V_{IN} UVLO UVLO OFF ON 0V Soft Start VOUT FB High Side **MOSFET Gate** Low Side **MOSFET Gate** UVLO Normal operation Normal operation Figure 50. UVLO Timing Chart

(5) Thermal Shutdown Function When the chip temperature exceeds Tj=175°C(Typ), the DC/DC converter output is stopped. Thermal protection circuit resets when the temperature falls. The circuit has a hysteresis of 25°C (Typ). The thermal shutdown circuit is intended for shutting down the device from thermal runaway in an abnormal state with the temperature exceeding Tjmax=150°C. It is not meant to protect or guarantee the soundness of the application. Do not use the function of this circuit for application protection design.

When thermal shut down circuit operates, the device will shut down and re-start in hiccup mode after 8ms(Typ).

Application Example (Vout=1V, Fosc=300kHz)

Parameter	Symbol	Value
Input Voltage	V _{IN}	12 V
Output Voltage	Vout	1 V
Switching Frequency	Fosc	300kHz(Typ)
Maximum Output Current	Іомах	8A

Caution: Tj must be lower than 150°C under actual operating environment.

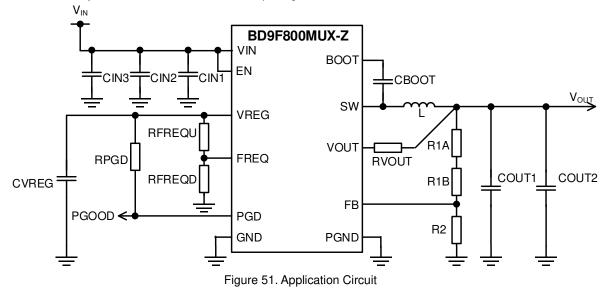


Table 1. Recommended Component Values

Part No.	Value	Company	Part Name
R1A	0 Ω	ROHM	MCR01MZPJ000
R1B	6.8 kΩ	ROHM	MCR01MZPD6801
R2	22 kΩ	ROHM	MCR01MZPD2202
RPGD	100 kΩ	ROHM	MCR01MZPJ104
RFREQU	-	-	-
RFREQD	10 kΩ	ROHM	MCR01MZPJ103
RVOUT	0 Ω	ROHM	MCR01MZPJ000
CIN1 ^(Note 1)	0.1 µF	Murata	GRM155R61H104ME14
CIN2 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
CIN3 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
COUT1 (Note 3)	47 µF	Murata	GRM31CR60J476ME19
COUT2 ^(Note 3)	22 µF	Murata	GRM21BR60J226ME39
CBOOT ^(Note 4)	0.1 µF	Murata	GRM152R61A104ME19
CVREG ^(Note 5)	2.2 µF	Murata	GRM188R61A225KE34
L	2.2µH	Murata	FDVE1040-H-2R2M

(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1µF ceramic capacitor as close as possible to the VIN pin and the PGND pin if needed.

(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 10µF(300kHz).

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Please confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet. A ceramic capacitor is recommended for the output capacitor.

(Note 4) For the capacitance of bootstrap capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set minimum value to no less than 0.047µF.

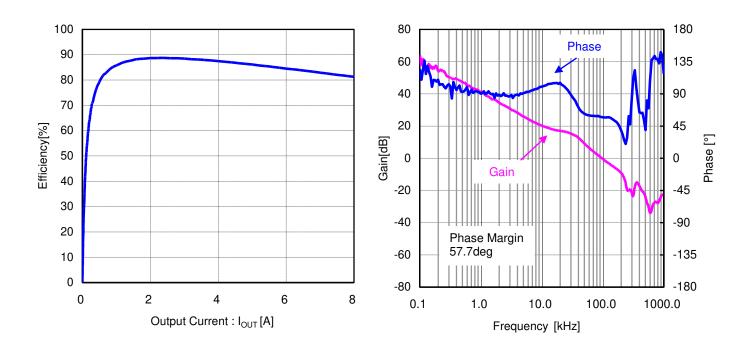
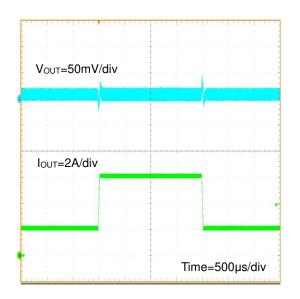
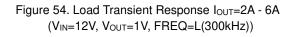


Figure 52. Efficiency vs Output Current $(V_{IN}=12V, V_{OUT}=1V, FREQ=L(300kHz))$

Figure 53. Loop Response I_{OUT}=8A (V_{IN}=12V, V_{OUT}=1V, FREQ=L(300kHz))





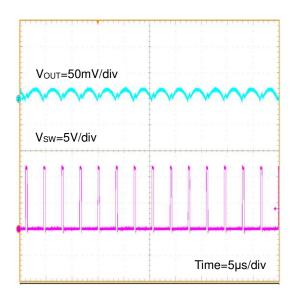


Figure 55. Vout Ripple Iout=8A (V_{IN}=12V, V_{OUT}=1V, FREQ=L(300kHz))

Application Example (Vout=1V, Fosc=600kHz)

Parameter	Symbol	Value
Input Voltage	VIN	12 V
Output Voltage	V _{OUT}	1 V
Switching Frequency	Fosc	600kHz(Typ)
Maximum Output Current	IOMAX	8A

Caution: Tj must be lower than 150°C under actual operating environment.

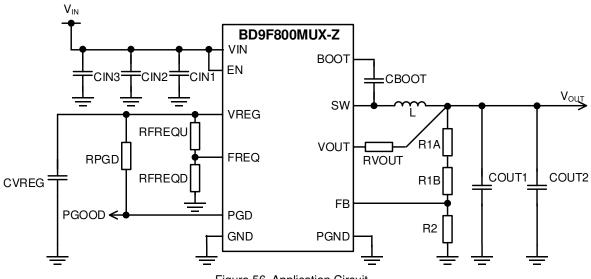


Figure 56. Application Circuit

D . N		2	
Part No.	Value	Company	Part Name
R1A	0 Ω	ROHM	MCR01MZPJ000
R1B	6.8 kΩ	ROHM	MCR01MZPD6801
R2	22 kΩ	ROHM	MCR01MZPD2202
RPGD	100 kΩ	ROHM	MCR01MZPJ104
RFREQU	10 kΩ	ROHM	MCR01MZPJ103
RFREQD	-	-	-
RVOUT	0 Ω	ROHM	MCR01MZPJ000
CIN1 ^(Note 1)	0.1 µF	Murata	GRM155R61H104ME14
CIN2 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
CIN3 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
COUT1 (Note 3)	47 µF	Murata	GRM31CR60J476ME19
COUT2 ^(Note 3)	-	-	-
CBOOT ^(Note 4)	0.1 µF	Murata	GRM152R61A104ME19
CVREG ^(Note 5)	2.2 μF	Murata	GRM188R61A225KE34
L	1.0µH	Murata	FDUE1040D-H-1R0M

(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1µF ceramic capacitor as close as possible to the VIN pin and the PGND pin if needed.

(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 6μF(600kHz).

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Please confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet. A ceramic capacitor is recommended for the output capacitor.

(Note 4) For the capacitance of bootstrap capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set minimum value to no less than 0.047µF.

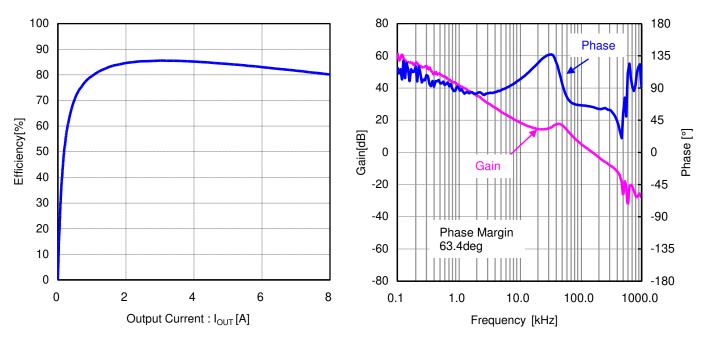


Figure 57. Efficiency vs Output Current (VIN=12V, VOUT=1V, FREQ=H(600kHz))

Figure 58. Loop Response I_{OUT} =8A (V_{IN} =12V, V_{OUT} =1V, FREQ=H(600kHz))

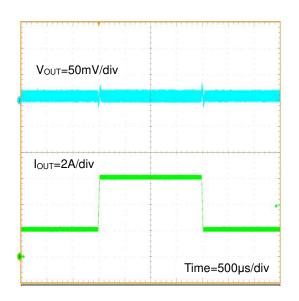


Figure 59. Load Transient Response I_{OUT} =2A - 6A (V_{IN}=12V, V_{OUT}=1V, FREQ=H(600kHz))

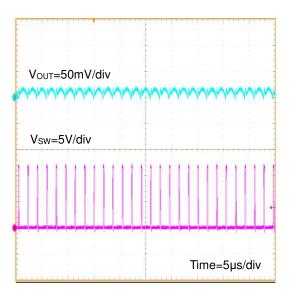


Figure 60. Vout Ripple Iout=8A (VIN=12V, Vout=1V, FREQ=H(600kHz))

Application Example (Vout=1.2V, Fosc=300kHz)

Parameter	Symbol	Value
Input Voltage	V _{IN}	12 V
Output Voltage	Vout	1.2 V
Switching Frequency	Fosc	300kHz(Typ)
Maximum Output Current	Іомах	8A

Caution: Tj must be lower than 150°C under actual operating environment.

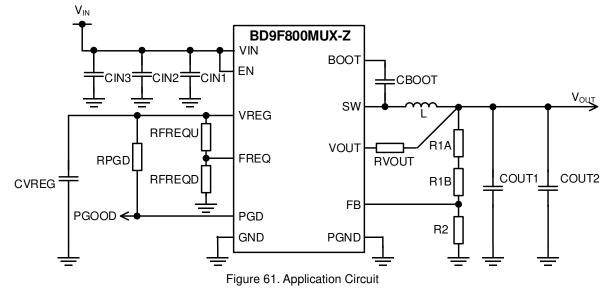


Table 3. Recommended Component Values

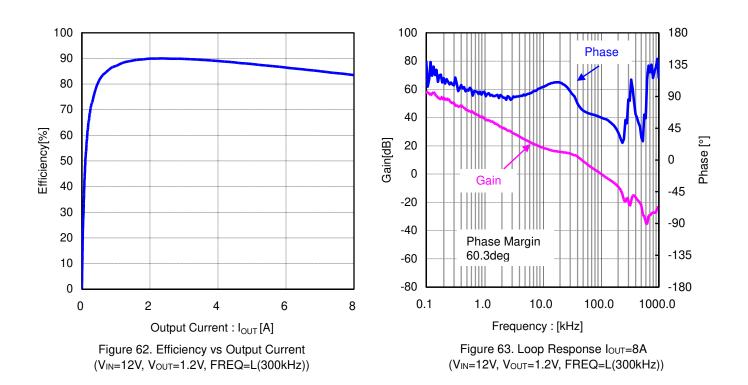
Part No.	Value	Company	Part Name
		Company	
R1A	0 Ω	ROHM	MCR01MZPJ000
R1B	6.8 kΩ	ROHM	MCR01MZPD6801
R2	12 kΩ	ROHM	MCR01MZPD1202
RPGD	100 kΩ	ROHM	MCR01MZPJ104
RFREQU	-	-	-
RFREQD	10 kΩ	ROHM	MCR01MZPJ103
RVOUT	0 Ω	ROHM	MCR01MZPJ000
CIN1 ^(Note 1)	0.1 µF	Murata	GRM155R61H104ME14
CIN2 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
CIN3 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
COUT1 ^(Note 3)	47 µF	Murata	GRM31CR60J476ME19
COUT2 ^(Note 3)	22 µF	Murata	GRM21BR60J226ME39
CBOOT ^(Note 4)	0.1 µF	Murata	GRM152R61A104ME19
CVREG ^(Note 5)	2.2 µF	Murata	GRM188R61A225KE34
L	2.2µH	Murata	FDVE1040-H-2R2M

(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1µF ceramic capacitor as close as possible to the VIN pin and the PGND pin if needed.

(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 10µF(300kHz).

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Please confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet. A ceramic capacitor is recommended for the output capacitor.

(Note 4) For the capacitance of bootstrap capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set minimum value to no less than 0.047µF.



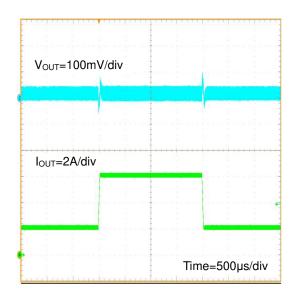


Figure 64. Load Transient Response $I_{OUT}=2A - 6A$ (VIN=12V, VOUT=1.2V, FREQ=L(300kHz))

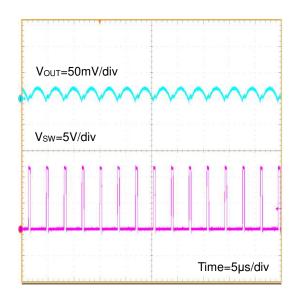


Figure 65. Vout Ripple Iout=8A (V_{IN}=12V, V_{OUT}=1.2V, FREQ=L(300kHz))

Application Example (Vout=1.2V, Fosc=600kHz)

Parameter	Symbol	Value
Input Voltage	V _{IN}	12 V
Output Voltage	Vout	1.2 V
Switching Frequency	Fosc	600kHz(Typ)
Maximum Output Current	Іомах	8A

Caution: Tj must be lower than 150°C under actual operating environment.

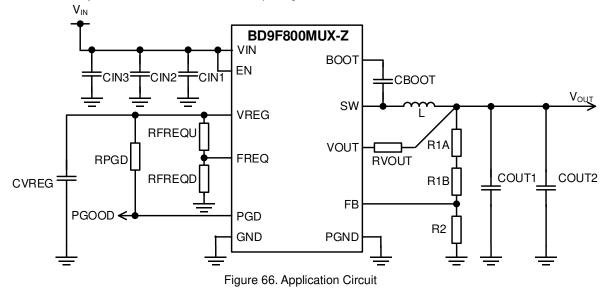


Table 4. Recommended Component Values

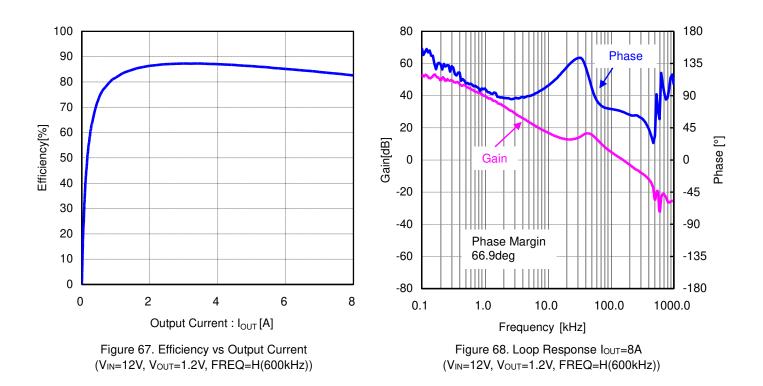
Part No.	Value	Company	Part Name
R1A	0 Ω	ROHM	MCR01MZPJ000
R1B	6.8 kΩ	ROHM	MCR01MZPD6801
R2	12 kΩ	ROHM	MCR01MZPD1202
RPGD	100 kΩ	ROHM	MCR01MZPJ104
RFREQU	10 kΩ	ROHM	MCR01MZPJ103
RFREQD	-	-	-
RVOUT	0 Ω	ROHM	MCR01MZPJ000
CIN1 ^(Note 1)	0.1 µF	Murata	GRM155R61H104ME14
CIN2 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
CIN3 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
COUT1 ^(Note 3)	47 µF	Murata	GRM31CR60J476ME19
COUT2 ^(Note 3)	-	-	-
CBOOT ^(Note 4)	0.1 µF	Murata	GRM152R61A104ME19
CVREG ^(Note 5)	2.2 µF	Murata	GRM188R61A225KE34
L	1.0µH	Murata	FDUE1040D-H-1R0M

(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1µF ceramic capacitor as close as possible to the VIN pin and the PGND pin if needed.

(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 6µF(600kHz).

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Please confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet. A ceramic capacitor is recommended for the output capacitor.

(Note 4) For the capacitance of bootstrap capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set minimum value to no less than 0.047µF.



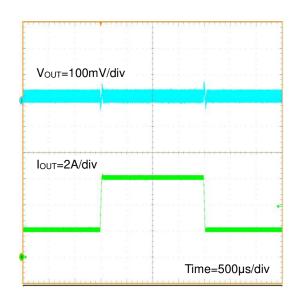


Figure 69. Load Transient Response I_{OUT} =2A - 6A (V_{IN}=12V, V_{OUT}=1.2V, FREQ=H(600kHz))

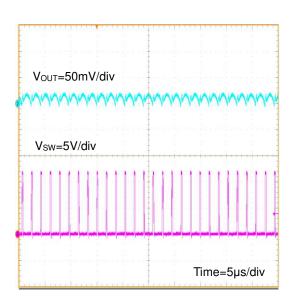
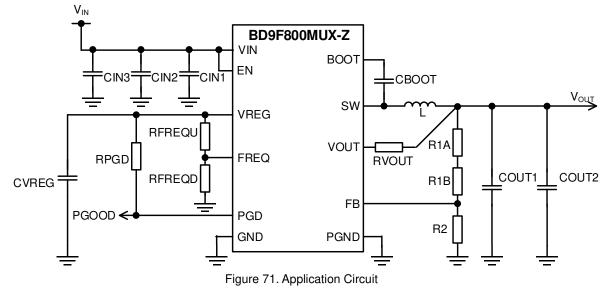


Figure 70. V_{OUT} Ripple I_{OUT}=8A (V_{IN}=12V, V_{OUT}=1.2V, FREQ=H(600kHz))

Application Example (Vout=3.3V, Fosc=300kHz)

Parameter	Symbol	Value
Input Voltage	V _{IN}	12 V
Output Voltage	Vout	3.3 V
Switching Frequency	Fosc	300kHz(Typ)
Maximum Output Current	Іомах	8A

Caution: Tj must be lower than 150°C under actual operating environment.



Part No.	Value	Company	Part Name
R1A	5.1 kΩ	ROHM	MCR01MZPD5101
R1B	68 kΩ	ROHM	MCR01MZPD6802
R2	22 kΩ	ROHM	MCR01MZPD2202
RPGD	100 kΩ	ROHM	MCR01MZPJ104
RFREQU	-	-	-
RFREQD	10 kΩ	ROHM	MCR01MZPJ103
RVOUT	0 Ω	ROHM	MCR01MZPJ000
CIN1 ^(Note 1)	0.1 µF	Murata	GRM155R61H104ME14
CIN2 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
CIN3 ^(Note 2)	10 µFV	Murata	GRM32ER61H106MA12
COUT1 ^(Note 3)	47 µF	Murata	GRM32ER61A476ME20
COUT2 ^(Note 3)	22 µF	Murata	GRM31CR61A226ME19
CBOOT ^(Note 4)	0.1 µF	Murata	GRM152R61A104ME19
CVREG ^(Note 5)	2.2 µF	Murata	GRM188R61A225KE34
L	3.3µH	Murata	FDVE1040-H-3R3M

(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1µF ceramic capacitor as close as possible to the VIN pin and the PGND pin if needed.

(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 10µF(300kHz).

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Please confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet. A ceramic capacitor is recommended for the output capacitor.

(Note 4) For the capacitance of bootstrap capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set minimum value to no less than 0.047µF.

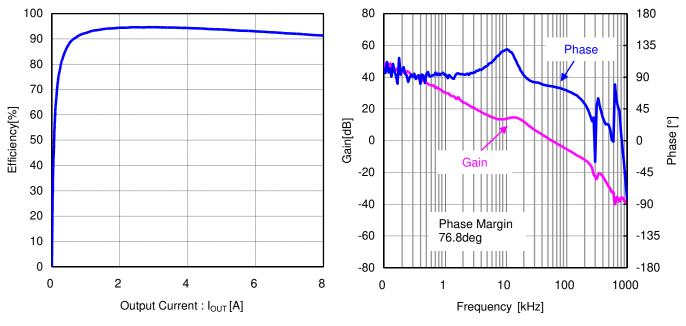


Figure 72. Efficiency vs Output Current (VIN=12V, VOUT=3.3V, FREQ=L(300kHz))

Figure 73. Loop Response I_{OUT}=8A (V_{IN} =12V, V_{OUT} =3.3V, FREQ=L(300kHz))

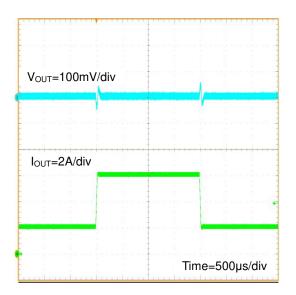


Figure 74. Load Transient Response I_{OUT} =2A - 6A (VIN=12V, VOUT=3.3V, FREQ=L(300kHz))

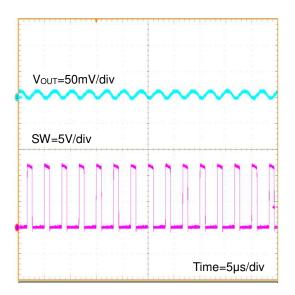


Figure 75. Vout Ripple Iout=8A (VIN=12V, Vout=3.3V, FREQ=L(300kHz))

Application Example (Vout=3.3V, Fosc=600kHz)

Parameter	Symbol	Value
Input Voltage	V _{IN}	12 V
Output Voltage	Vout	3.3 V
Switching Frequency	Fosc	600kHz(Typ)
Maximum Output Current	Іомах	8A

Caution: Tj must be lower than 150°C under actual operating environment.

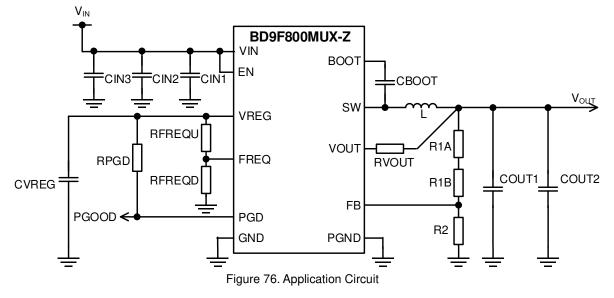


Table 6. Recommended Component Values

	1		
Part No.	Value	Company	Part Name
R1A	5.1 kΩ	ROHM	MCR01MZPD5101
R1B	68 kΩ	ROHM	MCR01MZPD6802
R2	22 kΩ	ROHM	MCR01MZPD2202
RPGD	100 kΩ	ROHM	MCR01MZPJ104
RFREQU	10 kΩ	ROHM	MCR01MZPJ103
RFREQD	-	-	-
RVOUT	0 Ω	ROHM	MCR01MZPJ000
CIN1 ^(Note 1)	0.1 µF	Murata	GRM155R61H104ME14
CIN2 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
CIN3 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
COUT1 (Note 3)	47 µF	Murata	GRM32ER61A476ME20
COUT2 ^(Note 3)	-	-	-
CBOOT ^(Note 4)	0.1 µF	Murata	GRM152R61A104ME19
CVREG ^(Note 5)	2.2 µF	Murata	GRM188R61A225KE34
L	1.5µH	Murata	FDVE1040-H-1R5M

(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1µF ceramic capacitor as close as possible to the VIN pin and the PGND pin if needed.

(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 6µF(600kHz).

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Please confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet. A ceramic capacitor is recommended for the output capacitor.

(Note 4) For the capacitance of bootstrap capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set minimum value to no less than 0.047µF.

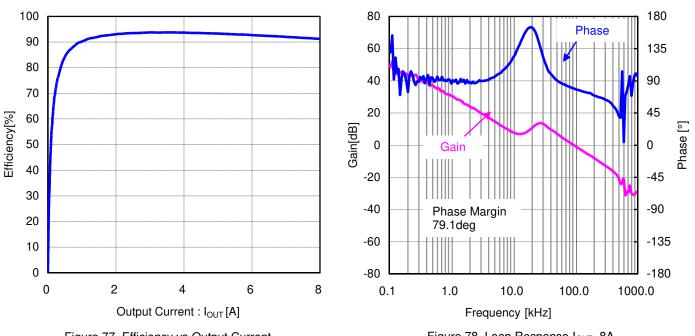


Figure 77. Efficiency vs Output Current (V_{IN} =12V, V_{OUT} =3.3V, FREQ=H(600kHz))



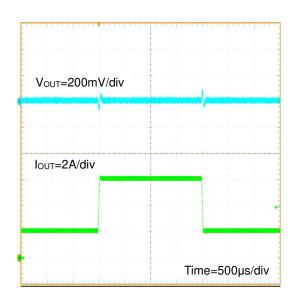


Figure 79. Load Transient Response I_{OUT} =2A - 6A (V_{IN}=12V, V_{OUT}=3.3V, FREQ=H(600kHz))

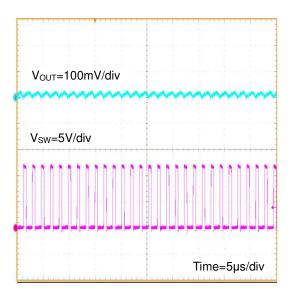


Figure 80. Vout Ripple Iout=8A (VIN=12V, Vout=3.3V, FREQ=H(600kHz))

Application Example (Vout=5V, Fosc=300kHz)

Parameter	Symbol	Value
Input Voltage	V _{IN}	12 V
Output Voltage	Vout	5 V
Switching Frequency	Fosc	300kHz(Typ)
Maximum Output Current	Іомах	8A

Caution: Tj must be lower than 150°C under actual operating environment.

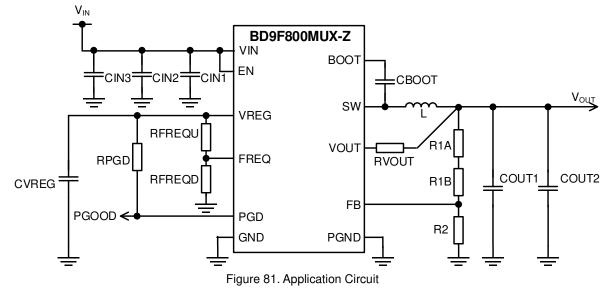


Table 7. Recommended Component Values

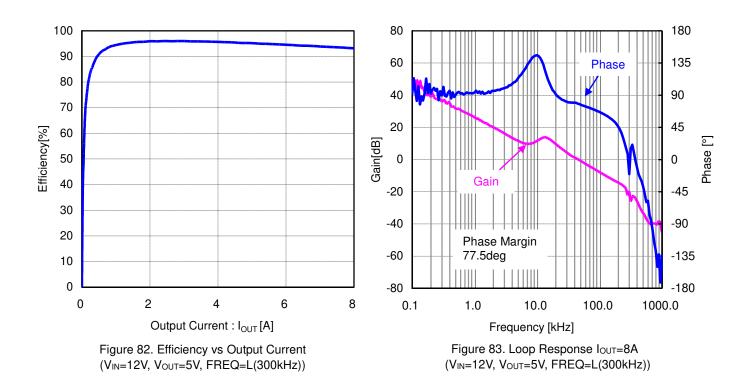
Part No.	Value	Company	Part Name
R1A	8.2k Ω	ROHM	MCR01MZPD8201
R1B	47 kΩ	ROHM	MCR01MZPD4702
R2	10 kΩ	ROHM	MCR01MZPD1002
RPGD	100 kΩ	ROHM	MCR01MZPJ104
RFREQU	-	-	-
RFREQD	10 kΩ	ROHM	MCR01MZPJ103
RVOUT	10 Ω	ROHM	MCR01MZPJ100
CIN1 ^(Note 1)	0.1 µF	Murata	GRM155R61H104ME14
CIN2 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
CIN3 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
COUT1 (Note 3)	47 µF	Murata	GRM32ER61A476ME20
COUT2 ^(Note 3)	22 µF	Murata	GRM31CR61A226ME19
CBOOT ^(Note 4)	0.1 µF	Murata	GRM152R61A104ME19
CVREG ^(Note 5)	2.2 µF	Murata	GRM188R61A225KE34
L	4.7µH	Murata	FDVE1040-H-4R7M

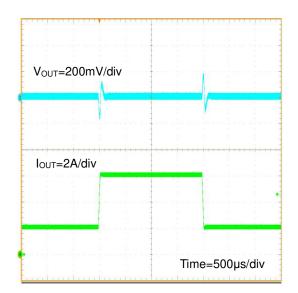
(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1µF ceramic capacitor as close as possible to the VIN pin and the PGND pin if needed.

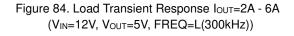
(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 10µF(300kHz).

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Please confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet. A ceramic capacitor is recommended for the output capacitor.

(Note 4) For the capacitance of bootstrap capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set minimum value to no less than 0.047µF.







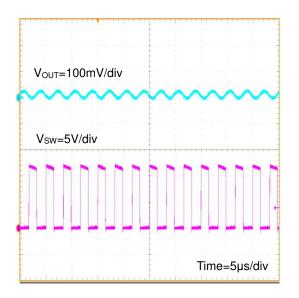
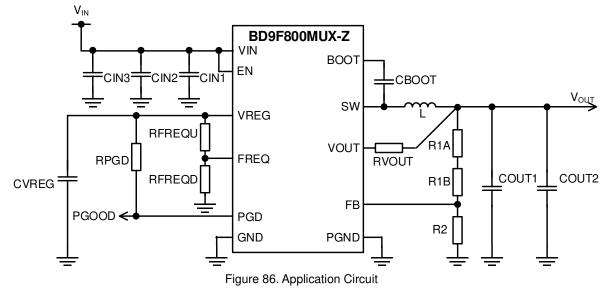


Figure 85. V_{OUT} Ripple I_{OUT}=8A (V_{IN}=12V, V_{OUT}=5V, FREQ=L(300kHz))

Application Example (V_{OUT}=5V, F_{OSC}=600kHz)

S			
Parameter	Symbol	Value	
Input Voltage	V _{IN}	12 V	
Output Voltage	Vout	5 V	
Switching Frequency	Fosc	600kHz(Typ)	
Maximum Output Current	Іомах	8A	

Caution: Tj must be lower than 150°C under actual operating environment.



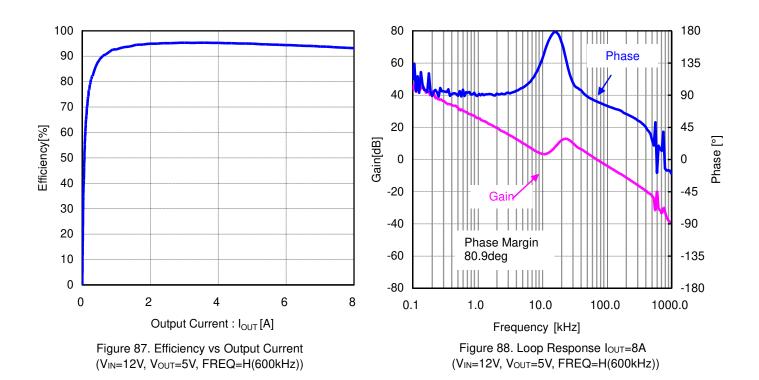
Part No.	Value	Company	Part Name
R1A	8.2k Ω	ROHM	MCR01MZPD8201
R1B	47 kΩ	ROHM	MCR01MZPD4702
R2	10 kΩ	ROHM	MCR01MZPD1002
RPGD	100 kΩ	ROHM	MCR01MZPJ104
RFREQU	10 kΩ	ROHM	MCR01MZPJ103
RFREQD	-	-	-
RVOUT	10 Ω	ROHM	MCR01MZPJ100
CIN1 ^(Note 1)	0.1 µF	Murata	GRM155R61H104ME14
CIN2 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
CIN3 ^(Note 2)	10 µF	Murata	GRM32ER61H106MA12
COUT1 (Note 3)	47 µF	Murata	GRM32ER61A476ME20
COUT2 ^(Note 3)	-	-	-
CBOOT ^(Note 4)	0.1 µF	Murata	GRM152R61A104ME19
CVREG ^(Note 5)	2.2 µF	Murata	GRM188R61A225KE34
L	2.2µH	Murata	FDVE1040-H-2R2M

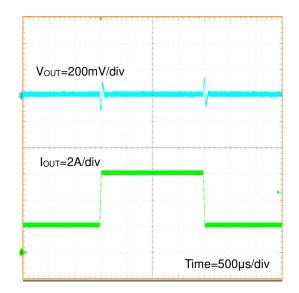
(Note 1) In order to reduce the influence of high frequency noise, connect a 0.1µF ceramic capacitor as close as possible to the VIN pin and the PGND pin if needed.

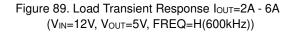
(Note 2) For the capacitance of input capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set to a minimum value of no less than 6µF(600kHz).

(Note 3) In case capacitance value fluctuates due to temperature characteristics, DC bias characteristics, etc. of the output capacitor, loop response characteristics may change. Please confirm on the actual equipment. When selecting a capacitor, confirm the characteristics of the capacitor in its datasheet. A ceramic capacitor is recommended for the output capacitor.

(Note 4) For the capacitance of bootstrap capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set minimum value to no less than 0.047µF.







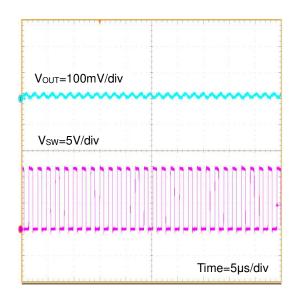


Figure 90. V_{OUT} Ripple I_{OUT}=8A (V_{IN}=12V, V_{OUT}=5V, FREQ=H(600kHz))

Selection of Components Externally Connected

About the application except the recommendation, please contact us.

1. Output LC Filter

In order to supply a continuous current to the load, the DC/DC converter requires an LC filter for smoothing the output voltage. The recommended inductance value is listed in Table 9.

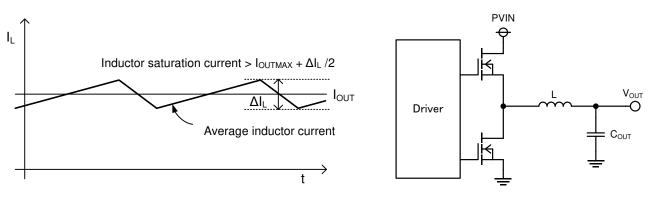


Figure 91. Waveform of current through inductor

Figure 92. Output LC filter circuit

Inductor ripple current ΔI_{L} can be represented by the following equation.

$$\Delta I_{L} = V_{OUT} \times (V_{IN} - V_{OUT}) \times \frac{1}{V_{IN} \times f_{SW} \times L} = 1528 \text{ [mA]}$$
Where:

$$V_{IN} = 12V$$

$$V_{OUT} = 1.0V$$

$$L = 1.0\mu\text{H}$$

$$f_{SW} = 600\text{kHz}$$

The saturation current of the inductor must be larger than the sum of the maximum output current and 1/2 of the inductor ripple current ΔI_L .

Table 9.	Recommended	inductance value
10010 01	1.0000111110110000	induotantoo valao

Frequency	Output Voltage				
	1.0V	1.2V	3.3V	5.0V	12V
300kHz	2.2µH	2.2µH	3.3µH	4.7µH	5.6µH
600kHz	1.0µH	1.0µH	1.5µH	2.2µH	3.3µH

The output capacitor C_{OUT} affects the output ripple voltage characteristics. The output capacitor C_{OUT} must satisfy the required ripple voltage characteristics.

The output ripple voltage can be represented by the following equation.

$$\Delta V_{RPL} = \Delta I_L \times (R_{ESR} + \frac{1}{8 \times C_{OUT} \times f_{SW}}) [v]$$

Where:

RESR is the Equivalent Series Resistance (ESR) of the output capacitor.

* The capacitor rating must allow a sufficient margin with respect to the output voltage. The output ripple voltage is decreased with a smaller R_{ESR} . Considering temperature and DC bias characteristics, please use ceramic capacitor of about 66µF to 100µF(300kHz), or 44µF to 100µF(600kHz).

* Be careful of total capacitance value, when additional capacitor C_{LOAD} is connected in addition to output capacitor C_{OUT}. Use maximum additional capacitor C_{LOAD} (Max) which satisfies the following condition.

Maximum starting inductor bottom ripple current I_{LSTART} < Current Limit Threshold 8.5[A] (Min)

Maximum starting inductor bottom ripple current ILSTART can be expressed using the following equation.

 $I_{LSTART} = Maximum starting output current(I_{OSS}) + Charge current to output capacitor(I_{CAP}) - \frac{\Delta I_L}{2}$

Charge current to output capacitor I_{CAP} can be expressed using the following equation.

$$I_{CAP} = \frac{(C_{OUT} + C_{LOAD}) \times V_{OUT}}{t_{SS}} [A]$$

* CLOAD has an effect on the stability of the DC/DC converter.

To ensure the stability of the DC/DC converter, make sure that a sufficient phase margin is provided.

2. Output Voltage Setting

The output voltage value can be set by the feedback resistance ratio. Please use resisters of about $1k\Omega$ to $100k\Omega$.

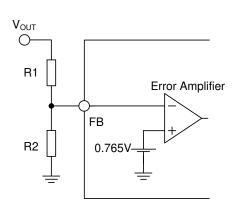


Figure 93. Feedback Resistor Circuit

$$V_{OUT} = \frac{R1 + R2}{R2} \times 0.765 \,[V]$$
$$R2 = \frac{0.765}{V_{OUT} - 0.765} \times R1 \,[\Omega]$$
$$0.765 [V] \le V_{OUT} \le 13.5 \,[V]$$

BD9F800MUX-Z operates under the condition which satisfies the following equation.

$$V_{IN} \times 0.033 [V] \le V_{OUT} \le V_{IN} \times 0.87 - 0.12 \times I_{OUT} [V] (300 \text{ kHz})$$

 $V_{IN} \times 0.067 [V] \leq V_{OUT} \leq V_{IN} \times 0.77 - 0.13 \times I_{OUT} [V] (600 \text{ kHz})$

3. Input Capacitor

Use a ceramic capacitor. It is more effective by placing it near VIN and PGND terminals. In using capacitor, please consider temperature and DC bias characteristics. For normal setting, it is recommended to connect two 10μ F and 0.1μ F capacitors. Input ripple voltage can be reduced further by using larger values. Also, considering temperature and DC bias characteristics, do not use capacity less than 10μ F(300kHz), 6μ F(600kHz). In order to reduce the influence of high frequency noise, place 0.1μ F ceramic capacitor close to VIN terminal and PGND terminal as much as possible.

4. VREG Capacitor

Connect a 2.2 μ F ceramic capacitor between VREG terminal and GND terminal. For the capacitance of VREG capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set minimum value to no less than 1 μ F. Place VREG capacitor close to VREG terminal and GND terminal as much as possible.

5. Bootstrap Capacitor

Connect a 0.1μ F ceramic capacitor between SW terminal and BOOT terminal. For the capacitance of bootstrap capacitor, take temperature characteristics, DC bias characteristics, etc. into consideration to set minimum value to no less than 0.047μ F. Place bootstrap capacitor close to BOOT terminal and SW terminal as much as possible.

PCB Layout Design

PCB layout design for DC/DC converter power supply IC is as important as the circuit design. Appropriate layout can avoid various problems caused by power supply circuit. Figure 94-a to 94-c show the current path in a buck converter circuit. The Loop1 in Figure 94-a is a current path when H-side Switch is ON and L-side Switch is OFF, the Loop2 in Figure 94-b is when H-side Switch is OFF and L-side Switch is ON. The thick line in Figure 94-c shows the difference between Loop1 and Loop2. The current in thick line changes sharply each time the switching element H-side and L-side Switch change from OFF to ON, and vice versa. These sharp changes induce several harmonics in the waveform. Therefore, the loop area of thick line that is consisted by input capacitor and IC should be as small as possible to minimize noise. For more detail, refer to application note of switching regulator series "PCB Layout Techniques of Buck Converter".

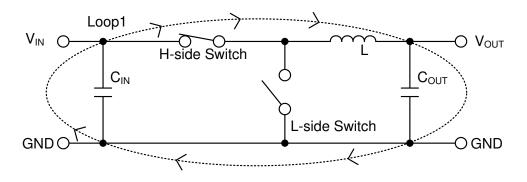


Figure 94-a. Current path when H-side Switch = ON, L-side switch = OFF

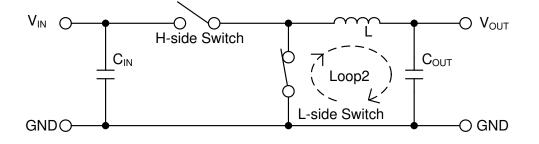


Figure 94-b. Current path when H-side Switch = OFF, L-side switch = ON

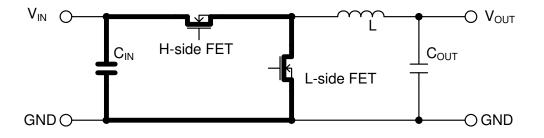


Figure 94-c. Difference of current and critical area in layout

PCB Layout Design - continued

When designing the PCB layout, please pay extra attention to the following points:

- Place input capacitor on the same PCB surface as the IC and as close as possible to the IC's VIN terminal and PGND terminal.
- If there is any unused area on the PCB, provide a copper foil plane for the ground node to assist heat dissipation from the IC and the surrounding components.
- Switching nodes should be traced as thick and short as possible to the inductor, because they may induce the noise to the other nodes due to AC coupling.
- Please keep the lines connected to FB away from the SW node as far as possible.
- Please place output capacitor away from input capacitor to avoid harmonics noise from the input.
- Please connect GND to PGND that are close to the output capacitor. It can avoid harmonic noise.

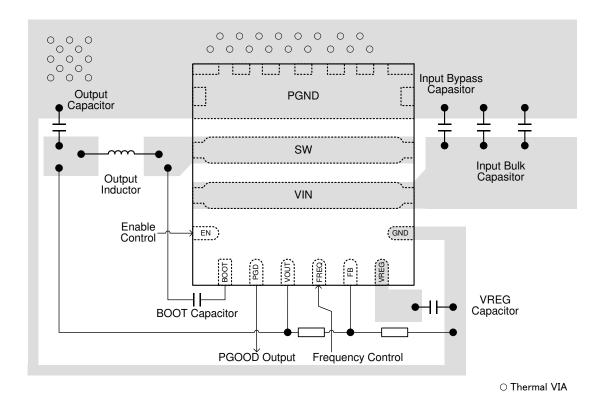
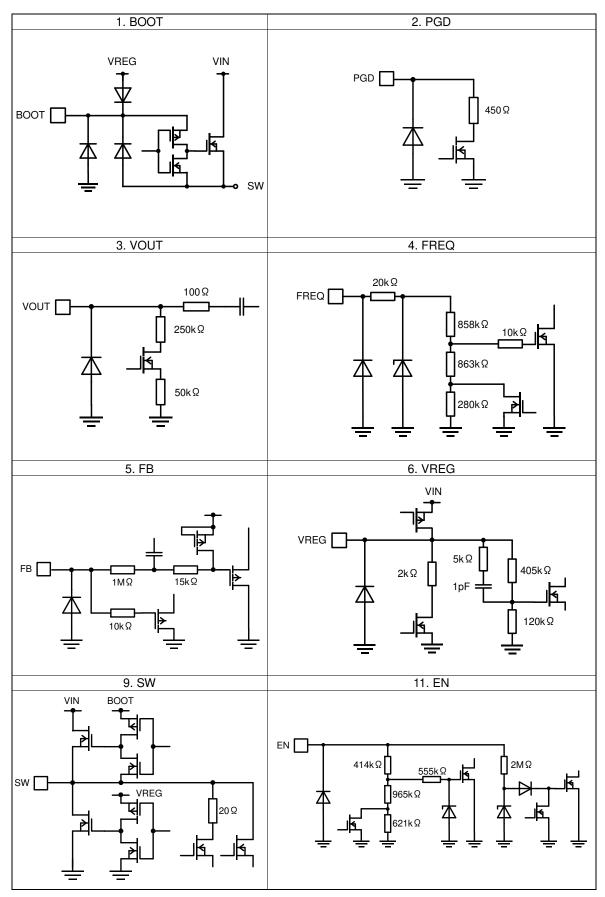
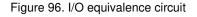


Figure 95. Example of PCB Layout (TOP VIEW)

I/O Equivalent Circuit





Operational Notes

1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply pins.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition. However, pins that drive inductive loads (e.g. motor driver outputs, DC-DC converter outputs) may inevitably go below ground due to back EMF or electromotive force. In such cases, the user should make sure that such voltages going below ground will not cause the IC and the system to malfunction by examining carefully all relevant factors and conditions such as motor characteristics, supply voltage, operating frequency and PCB wiring to name a few.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Recommended Operating Conditions

The function and operation of the IC are guaranteed within the range specified by the recommended operating conditions. The characteristic values are guaranteed only under the conditions of each item specified by the electrical characteristics.

6. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

7. Operation Under Strong Electromagnetic Field

Operating the IC in the presence of a strong electromagnetic field may cause the IC to malfunction.

8. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

9. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

10. Unused Input Pins

Input pins of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input pins should be connected to the power supply or ground line.

Operational Notes – continued

11. Regarding the Input Pin of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode. When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

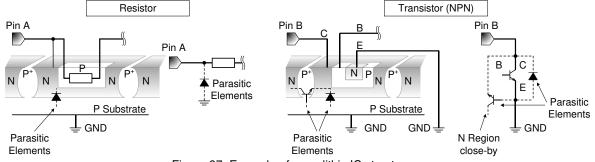


Figure 97. Example of monolithic IC structure

12. Ceramic Capacitor

When using a ceramic capacitor, determine a capacitance value considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

13. Area of Safe Operation (ASO)

Operate the IC such that the output voltage, output current, and the maximum junction temperature rating are all within the Area of Safe Operation (ASO).

14. Thermal Shutdown Circuit(TSD)

This IC has a built-in thermal shutdown circuit that prevents heat damage to the IC. Normal operation should always be within the IC's maximum junction temperature rating. If however the rating is exceeded for a continued period, the junction temperature (Tj) will rise which will activate the TSD circuit that will turn OFF power output pins. When the Tj falls below the TSD threshold, the circuits are automatically restored to normal operation.

Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

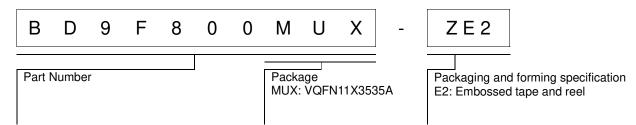
15. Over Current Protection Circuit (OCP)

This IC incorporates an integrated overcurrent protection circuit that is activated when the load is shorted. This protection circuit is effective in preventing damage due to sudden and unexpected incidents. However, the IC should not be used in applications characterized by continuous operation or transitioning of the protection circuit.

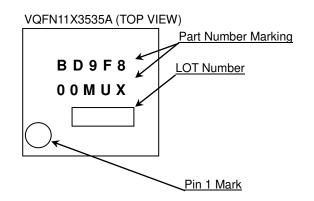
16. Disturbance Light

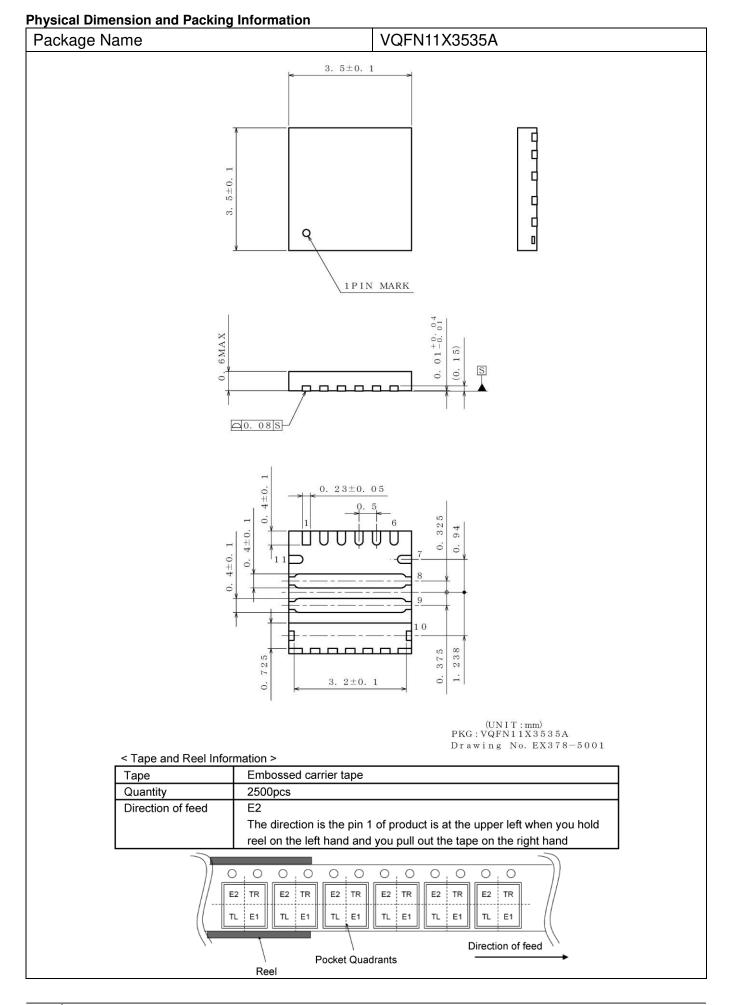
In a device where a portion of silicon is exposed to light such as in a WL-CSP and chip products, IC characteristics may be affected due to photoelectric effect. For this reason, it is recommended to come up with countermeasures that will prevent the chip from being exposed to light.

Ordering Information



Marking Diagram





Revision History

Date	Revision	Changes
31.Jul.2017	001	Created
19.Mar.2018	002	Revised Tape Quantity
27.Dec.2018	003	Revised Part Number

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JAPAN	USA	EU	CHINA
CLASSⅢ	CLASSⅢ	CLASS II b	CLASSII
CLASSⅣ	CLASSII	CLASSⅢ	CLASSI

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 - [d] the Products are exposed to high Electrostatic
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